2SK1842

Silicon N-Channel Junction FET

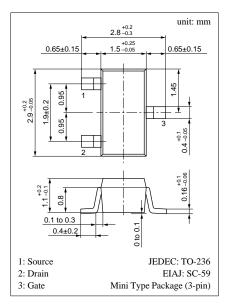
For impedance conversion in low frequency For infrared sensor

■ Features

- Low gate to source leakage current, I_{GSS}
- ullet Small capacitance of C_{iss} , C_{oss} , C_{rss}
- Mini-type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings (Ta = 25°C)

| Parameter | Symbol | Ratings | Unit |
|-----------------------------|------------------|-------------|------|
| Gate to Drain voltage | V_{GDO} | -40 | V |
| Gate to Source voltage | V _{GSO} | -40 | V |
| Drain current | I _D | 1 | mA |
| Gate current | I_G | 10 | mA |
| Allowable power dissipation | P _D | 150 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |



Marking Symbol (Example): EB

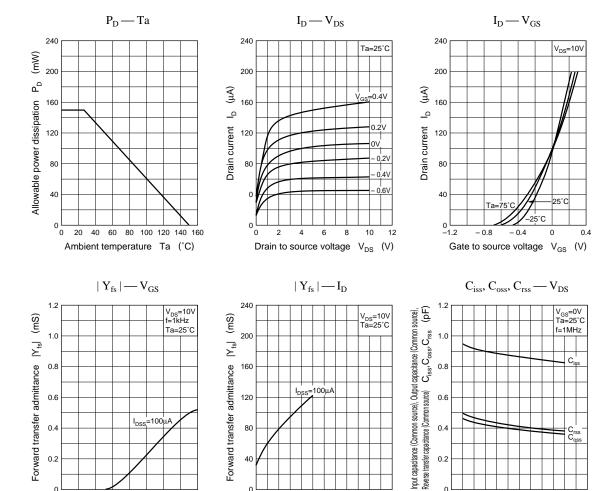
■ Electrical Characteristics (Ta = 25°C)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|--|-------------------|--------------------------------------|------|------|-------|------|
| Drain to Source cut-off current | ${\rm I_{DSS}}^*$ | $V_{DS} = 10V, V_{GS} = 0$ | 30 | | 200 | μA |
| Gate to Source leakage current | I_{GSS} | $V_{GS} = -20V, V_{DS} = 0$ | | | - 0.5 | nA |
| Gate to Drain voltage | V_{GDS} | $I_G = -10\mu A, V_{DS} = 0$ | -40 | | | V |
| Gate to Source cut-off voltage | V_{GSC} | $V_{DS} = 10V, I_D = 1\mu A$ | | -1.3 | -3 | V |
| Forward transfer admittance | $ Y_{fs} $ | $V_{DS} = 10V, V_{GS} = 0, f = 1kHz$ | 0.05 | | | mS |
| Input capacitance (Common Source) | C _{iss} | | | 1 | | pF |
| Output capacitance (Common Source) | Coss | $V_{DS} = 10V, V_{GS} = 0, f = 1MHz$ | | 0.4 | | pF |
| Reverse transfer capacitance (Common Source) | C _{rss} | | | 0.4 | | pF |

^{*} IDSS rank classification

| Runk | 0 | P | Q | R |
|-----------------------|----------|-----------|-----------|------------|
| I _{DSS} (mA) | 30 to 75 | 50 to 100 | 70 to 130 | 100 to 200 |
| Marking Symbol | EBP | EBQ | EBR | EBS |

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0.4

0.2

2

Drain to source voltage $\,V_{\rm DS}\,\,$ (V)

80

40

40 80 120 160

Drain current

 I_D (μA)

0.2

- 0.8

-0.4

Gate to source voltage V_{GS} (V)

0

0.4

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